CorEnergy

CE65E160DNHI

CorEnergy 650V GaN HEMT

Description

The CE65E160DNHI Series 650V, 160mΩ gallium nitride (GaN) FETs are normally-off devices. Corenergy GaN FETs offer better efficiency through lower gate charge, faster switching speeds, and smaller reverse recovery charge, delivering significant advantages over traditional silicon (Si) devices.

Corenergy is a leading-edge wide band gap supplier with world-class innovation .

Application

- Fast charger
- Renewable energy
- Telecom and data-com
- Servo motors
- Industrial
- Automotive

General Features

Low conduction and switching losses no free-wheeling diode required RoHS compliant and Halogen-free

Benefits

Increased efficiency through fast switching
Increased power density
Reduced system size and weight

Ordering Information

Part Number	Package	Package Configuration
CE65E160DNHI	DFN(8*8)	Source

Top

Bottom

Circuit Symbol

Features

BV$_{DSS}$	R$_{DSON}$	I$_{DS}$	Q$_G$
650V	160mΩ	13A	2.2nC

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Absolute Maximum Ratings

T_j=25°C unless otherwise stated

Symbol	Parameter		Limit value	Unit
$V_{DS,max}$	Drain to source voltage(T_j=-55°C to 150°C)		650	V
$V_{DS(transient)}$	Drain to source voltage-transient[a]		750	
V_{GS}	Gate to source voltage		-10~+7	
I_D	Continuous drain current @T_C=25°C[b]		13	A
	Continuous drain current @T_C=125°C[b]		6	
I_{DM}	Pulse drain current (pulse width: 300µs) @T_C=25°C		17	
	Pulse drain current (pulse width: 300µs) @T_C=125°C		10	
P_D	Maximum power dissipation @T_C=25°C		64	W
T_C	Operating temperature	Case	-55~150	°C
T_J		Junction	-55~150	°C
T_S	Storage temperature		-55~150	°C

Notes:

a.Non-repetitive events, T_{pulse} <200µs

b.For increased stability at high current operation

Thermal Resistance

Symbol	Parameter	Limit value	Unit
$R_{\theta JC}$	Junction-to-case	1.96	°C/W

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Electrical Parameters

T_j=25°C unless otherwise stated

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Forward Device Characteristics						
$V_{(BL)DSS}$	Drain-source voltage	650	-	-	V	V_{GS}=0V
$V_{GS(th)}$	Gate threshold voltage	2	2.5	3	V	I_D=10uA/mm, V_{DS}=1V, T_j=25°C
	Gate threshold voltage	-	2.8	-	V	I_D=10uA/mm, V_{DS}=1V, T_j=150°C
$R_{DS(on)}$	Drain-source on resistance	-	160	190	mΩ	V_{GS}=6V, I_D=1A, T_j=25°C
		-	330	-		V_{GS}=6V, I_D=1A, T_j=150°C
I_{DSS}	Drain-to-source leakage current	-	1	20	µA	V_{DS}=650V, V_{GS}=0V, T_j=25°C
		-	10	50		V_{DS}=650V, V_{GS}=0V, T_j=150°C
I_{GSS}	Gate-to-source forward leakage current	-	60	-	µA	V_{GS}=6V, V_{DS}=0V
C_{ISS}	Input capacitance	-	66	-	pF	V_{GS}=0V, V_{DS}=400V, f=1MHz
C_{OSS}	Output capacitance	-	26	-		
C_{RSS}	Reverse capacitance	-	0.9	-		
$C_{o(er)}$	Effective output capacitance (energy related)	-	48	-	pF	V_{GS}=0V, V_{DS}=0 to 400V
$C_{o(tr)}$	Effective output capacitance (time related)	-	68	-	pF	V_{GS}=0V, V_{DS}=0 to 400V
Q_{OSS}	Output Charge	-	27	-	nC	V_{GS}=0V, V_{DS}=0 to 400V
Q_G	Total gate charge	-	2.2	-	nC	V_{DS}=400V, V_{GS}=0 to 6V, I_D=1A
Q_{GS}	Gate-source charge	-	0.2	-		
Q_{GD}	Gate-drain charge	-	0.8	-		
$t_{d(on)}$	Turn-on delay time	-	2.65	-	nS	V_{DS}=400V, V_{GS}=0V to 6V, I_D=2.1A Rg_on(ext)= 6.8Ω Rg_off(ext)=2.2Ω, L=250uH
$t_{d(off)}$	Turn-off delay time	-	5.72	-		
t_r	Rise time	-	4.51	-		
t_f	Fall time	-	17.10	-		
Reverse Device Characteristics						
V_{SD}	Reverse voltage	-	3	-	V	V_{GS}=0V, I_{SD}=3A
Q_{RR}	Reversere recovery charge	-	0	-	nC	I_{SD}=3A, V_{DS}=400V

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Electrical Characteristics

T_j=25°C unless otherwise stated
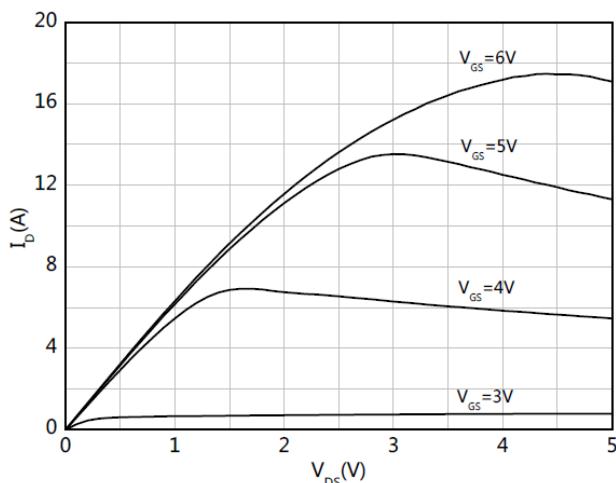

Figure 1. Typical Output Characteristics T_j=25°C
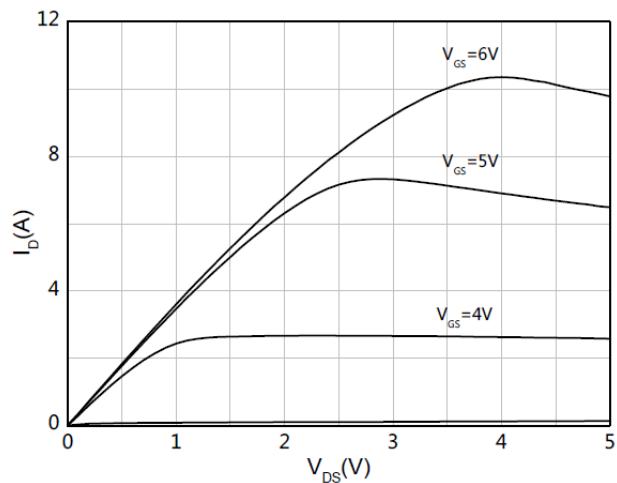

Figure 2. Typical Output Characteristics T_j=125°C
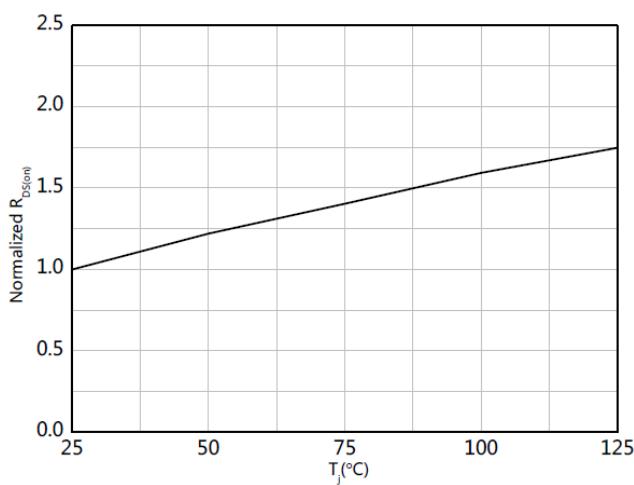
Figure 3. Drain-source On-state Resistance
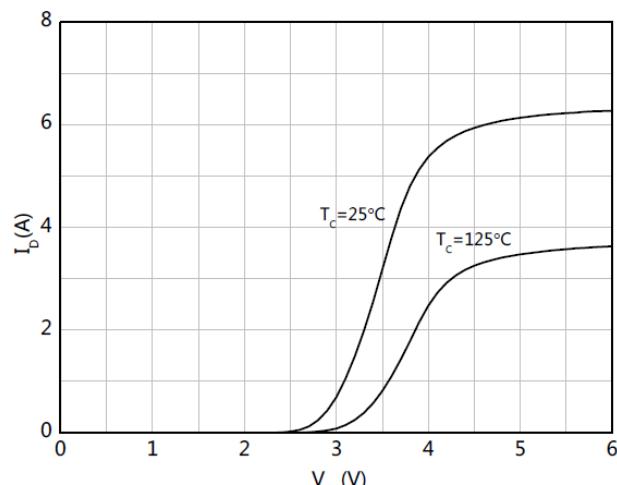
Figure 4. Typical Transfer Characteristics V_{DS}=1V

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T_j=25°C unless otherwise stated
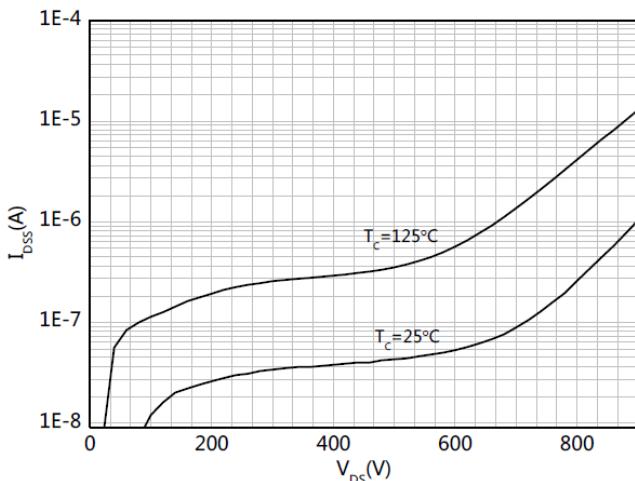
Figure 5. Drain-source Leakage Characteristics
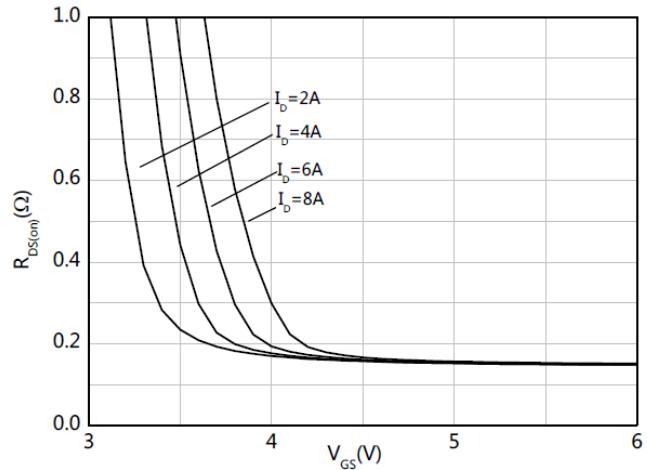
Figure 6. Typical On-state Resistance T_j=25°C
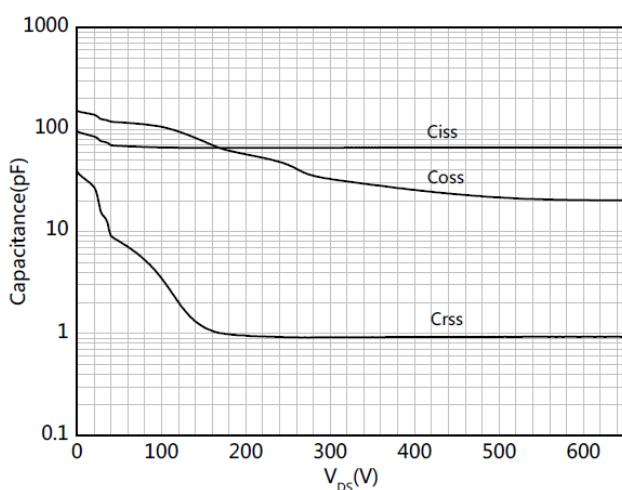
Figure 7. Typical Capacitance f =1MHz
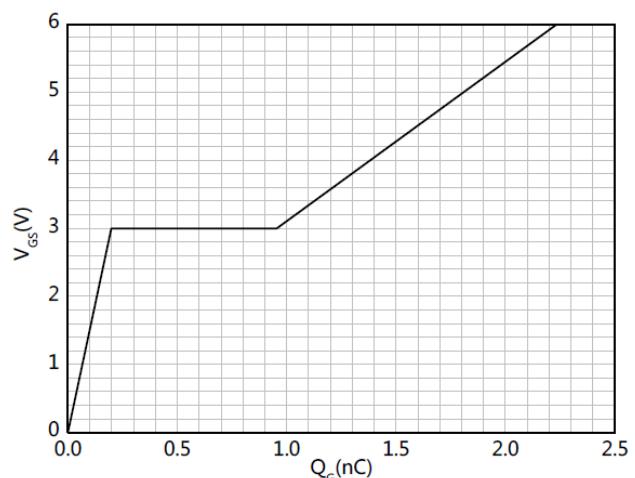
Figure 8. Typical Gate Charge (V_{DS}=400V, I_D=1A)

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Electrical Characteristics

T_j=25°C unless otherwise stated
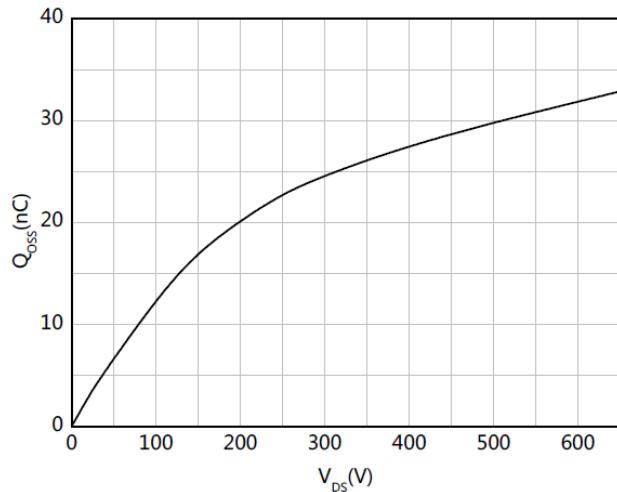
Figure 9. Typical Output Charge f=1MHz
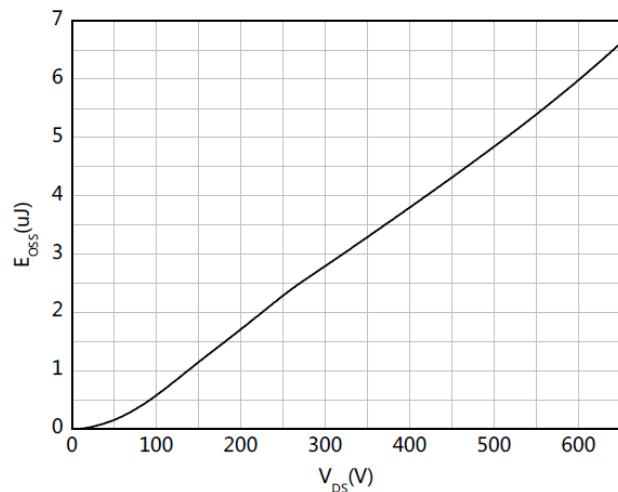
Figure 10. Typical Coss Stored Energy f=1MHz
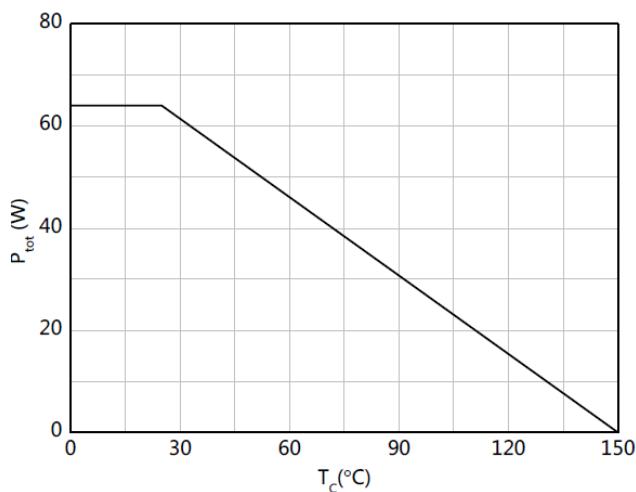
Figure 11. Power Dissipation
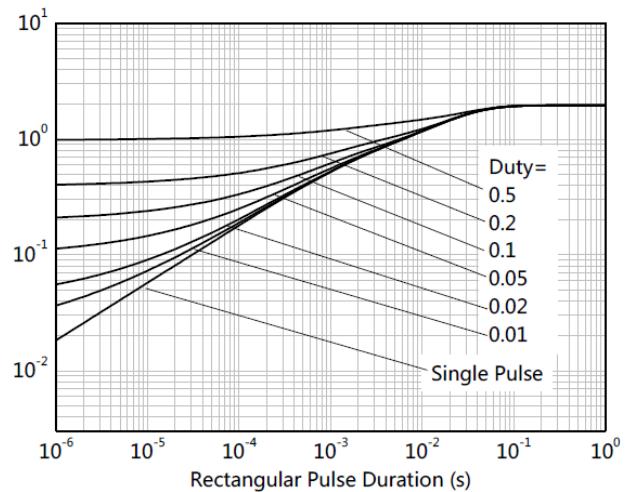
Figure 12. Transient Thermal Impedance

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Electrical Characteristics
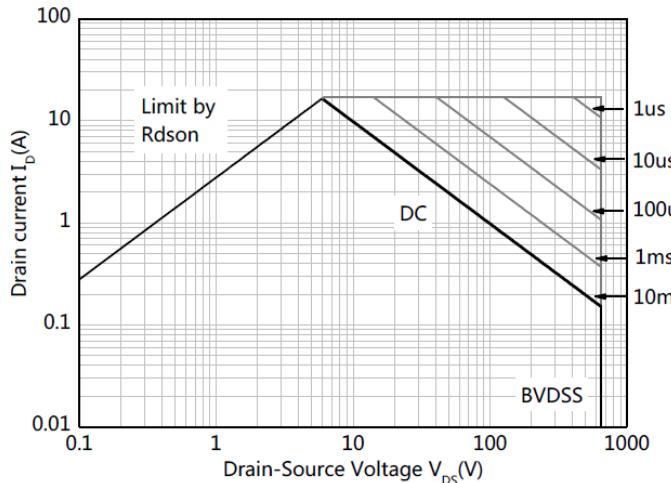
Figure 13. Safe Operation Area T_C=25°C
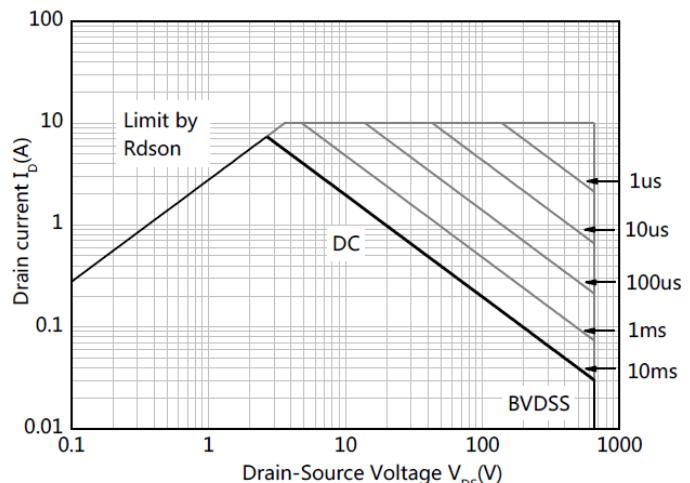

Figure 14. Safe Operation Area T_C=125°C
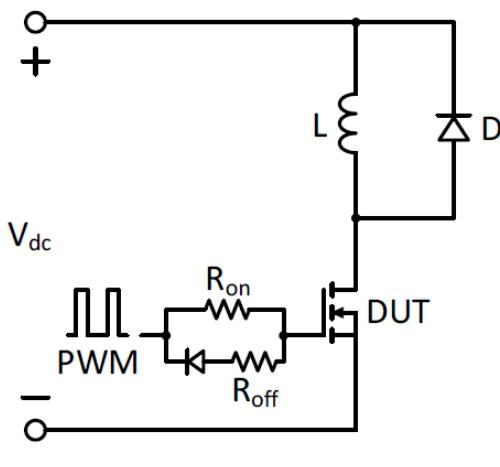
Figure 15. Switching Times With Inductive Load

V_{DS}=400V, V_{GS}=0V to 6V, I_D=2.1A,

$R_{G-on(ext)}$=6.8Ω, $R_{G-off(ext)}$=2.2Ω, L=250μH
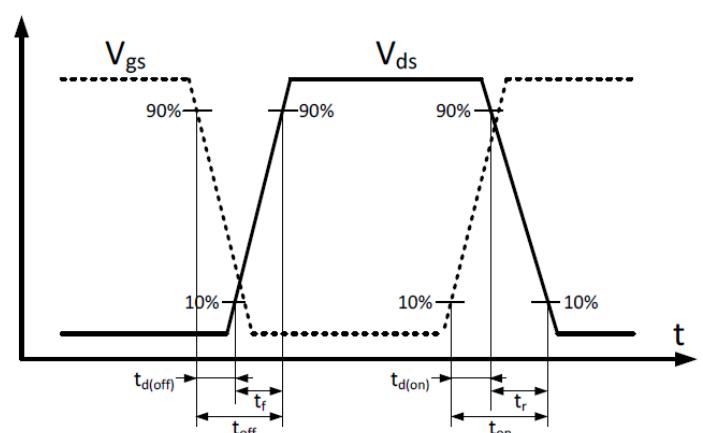
Figure 16. Switching Times With Waveform

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PACKAGE DIMENSIONS

DFN8*8-8L-A

Top view
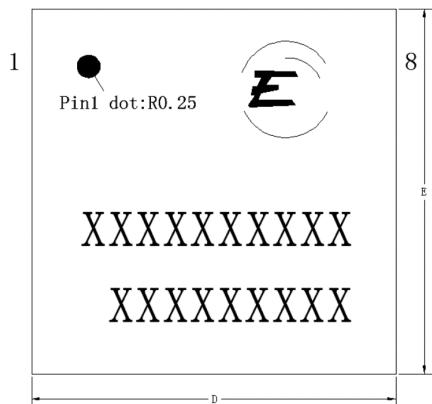
Bottom view
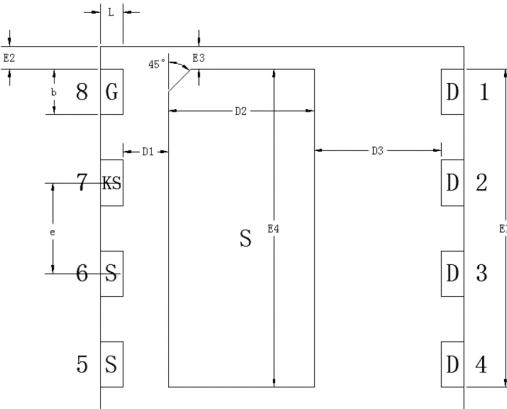
Side view(left/right)
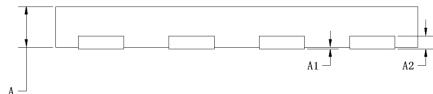
Symbol	Min. (mm)	Mean. (mm)	Max. (mm)
A	0.80	0.90	1.00
A1	0	0.02	0.05
A2	0.203REF		
D	7.9	8	8.1
E	7.9	8	8.1
D1	0.9	1	1.1
D2	3.1	3.2	3.3
D3	2.7	2.8	2.9
E1	6.9	7	7.1
E2	0.4	0.5	0.6
E3	0.4	0.5	0.6
E4	6.9	7	7.1
e	1.9	2	2.1
b	0.9	1	1.1
L	0.4	0.5	0.6